

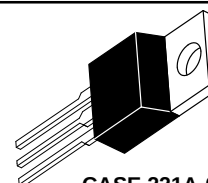
Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

... designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies; or wherever half-wave silicon gate-controlled, solid-state devices are needed.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts

**S2800
Series**

**SCRs
10 AMPERES RMS
50 thru 800 VOLTS**



**CASE 221A-04
(TO-220AB)
STYLE 3**

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ ($T_J = 25$ to 100°C , Gate Open)	V_{RRM} V_{DRM}		Volts
F A B D M N S2800		50 100 200 400 600 800	
Peak Non-repetitive Reverse Voltage and Non-Repetitive Off-State Voltage ⁽¹⁾	V_{RSM} V_{DSM}		Volts
F A B D M N S2800		75 125 250 500 700 900	
RMS Forward Current (All Conduction Angles) $T_C = 75^\circ\text{C}$	$I_T(\text{RMS})$	10	Amps
Peak Forward Surge Current (1 Cycle, Sine Wave, 60 Hz, $T_C = 80^\circ\text{C}$)	I_{TSM}	100	Amps
Circuit Fusing Considerations ($t = 8.3$ ms)	I^2t	40	A^2s
Forward Peak Gate Power ($t \leq 10$ μs)	P_{GM}	16	Watts
Forward Average Gate Power	$P_{G(AV)}$	0.5	Watt
Operating Junction Temperature Range	T_J	-40 to +100	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

S2800 Series

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$, Gate Open) $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_{DRM}, I_{RRM}	— —	— —	10 2	μA mA
Instantaneous On-State Voltage, ($I_{TM} = 30 \text{ A Peak}$, Pulse Width $\leq 1 \text{ ms}$, Duty Cycle $\leq 2\%$)	V_T	—	1.7	2	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_L = 30 \text{ Ohms}$)	I_{GT}	—	8	15	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_L = 30 \text{ Ohms}$)	V_{GT}	—	0.9	1.5	Volts
Holding Current (Gate Open, $V_D = 12 \text{ Vdc}$, $I_T = 150 \text{ mA}$)	I_H	—	10	20	mA
Gate Controlled Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 2 \text{ A}$, $I_{GR} = 80 \text{ mA}$)	t_{gt}	—	1.6	—	μs
Circuit Commutated Turn-Off Time ($V_D = V_{DRM}$, $I_{TM} = 2 \text{ A}$, Pulse Width = $50 \mu\text{s}$, $dv/dt = 200 \text{ V}/\mu\text{s}$, $di/dt = 10 \text{ A}/\mu\text{s}$, $T_C = 75^{\circ}\text{C}$)	t_q	—	25	—	μs
Critical Rate-of-Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Rise, $T_C = 100^{\circ}\text{C}$)	dv/dt	—	100	—	$\text{V}/\mu\text{s}$

FIGURE 1 – CURRENT DERATING

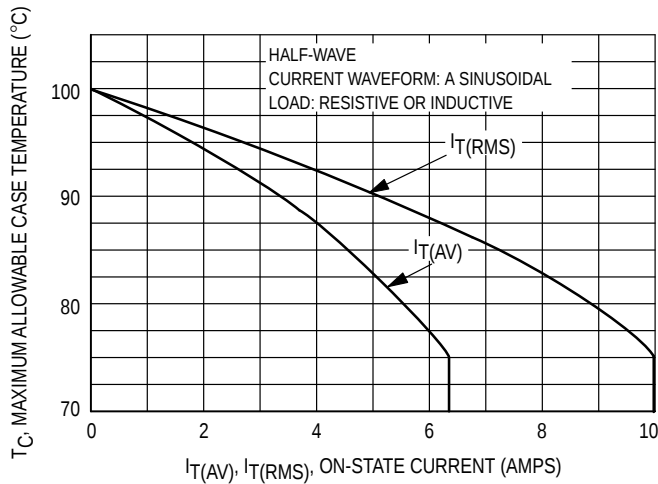
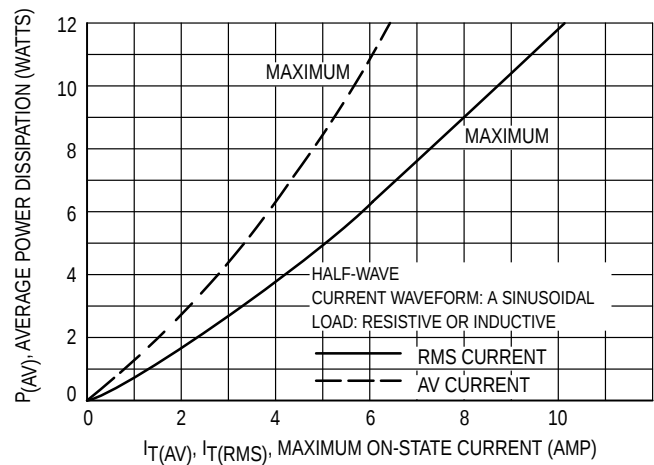
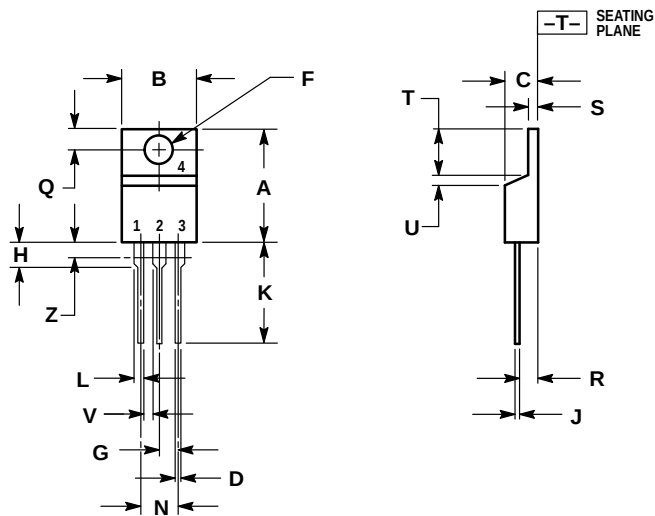


FIGURE 2 – POWER DISSIPATION



PACKAGE DIMENSIONS



STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

- NOTES:
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 - 2. CONTROLLING DIMENSION: INCH.
 - 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.055	1.15	1.39
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

CASE 221A-04
(TO-220AB)

S2800 Series

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and  are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

Literature Distribution Centers:

USA: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036.

EUROPE: Motorola Ltd.; European Literature Centre; 88 Tanners Drive, Blakelands, Milton Keynes, MK14 5BP, England.

JAPAN: Nippon Motorola Ltd.; 4-32-1, Nishi-Gotanda, Shinagawa-ku, Tokyo 141, Japan.

ASIA PACIFIC: Motorola Semiconductors H.K. Ltd.; Silicon Harbour Center, No. 2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong.



S2800/D

